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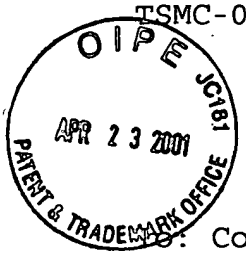
GAU 2812

TSMC-00-338



April 12, 2001

To: Commissioner of Patents and Trademarks
Washington, D.C. 20231

Fr: George O. Saile, Reg. No. 19,572
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Subject: Serial No. 09/785,114 02/20/01

Pin-Shyne Chin, Wen-Tye Yue,
Hsien-Chin Peng

A LOW LEAKAGE ONE TRANSISTOR STATIC RANDOM ACCESS MEMORY

Grp. Art Unit: 2812

INFORMATION DISCLOSURE STATEMENT

Enclosed is Form PTO-1449, Information Disclosure Citation In An Application.

The following Patents and/or Publications are submitted to comply with the duty of disclosure under CFR 1.97-1.99 and 37 CFR 1.56. Copies of each document is included herewith.

U.S. Patent 6,078,087 to Huang et al., "SRAM Memory Device with Improved Performance", discloses a TFT SRAM layout.

U.S. Patent 5,686,336 to Lee, "Method of Manufacture of Four Transistor SRAM Cell Layout", discloses a 4T SRAM layout.

U.S. Patent 5,953,606 to Huang et al., "Method for Manufacturing a TFT SRAM Memory Device with Improved Performance", discloses a TFT SRAM layout.

Sincerely,

Stephen B. Ackerman,
Reg. No. 37761